

WAFER PROCESSING METHOD

ABSTRACT OF THE DISCLOSURE

Disclosed herein is a wafer processing method including a ring-shaped modified layer forming step of forming a first ring-shaped modified layer and a second ring-shaped modified layer along a peripheral marginal area, a street modified layer forming step of forming a street modified layers along streets, and a dividing step of grinding a back surface of a wafer to form the wafer to a predetermined thickness and dividing the wafer into individual device chips by cracks extending from the street modified layers to the streets. In the street modified layer forming step, a focal point of a laser beam is positioned in such a manner that a start point and an end point of the street modified layer are positioned between the first ring-shaped modified layer and the second ring-shaped modified layer.

[Fig. 5A]